

METHOD FOR CLEANING A PROCESSING CHAMBER AND METHOD FOR MANUFACTURING A SEMICONDUCTOR DEVICE

ABSTRACT

5 A method for cleaning a processing chamber and manufacturing a
semiconductor device by removing impurities from a substrate in the processing
chamber with a plasma of a first gas including hydrogen gas. After the substrate is
removed from the processing chamber, the processing chamber is etched with the
plasma of a non-hydrogenous second gas. Thus, the etching selectivity can be
10 improved and the particles are prevented from depositing and/or forming on the
substrate.